

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	148727	"20" and (conduct\$3 near (layer\$1 film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 16:19
L2	172	(MTJ (magnetic near tunnel near junction)) near stack\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 16:32
L3	69	2 and (conduct\$3 near (layer\$1 film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 16:19
L4	8	3 and (low near k near (insulat\$3 oxide dielectric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 18:02
L5	1	("6376260").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/11 16:30
L6	15	(insulat\$3 oxide dielectric) with (between interpos\$3) with (MTJ (magnetic near tunnel near junction)) with (conduct\$3 near (layer\$1 film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 16:43
L7	44	(insulat\$3 oxide dielectric (black near diamond)) with (between interpos\$3) with (MTJ (magnetic near tunnel near junction)) with (((bit program) near line\$1) (conduct\$3 near (layer\$1 film\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 17:39
L8	1	("6201259").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/11 17:25
L9	0	(black near diamond) with (between interpos\$3) with (MTJ (magnetic near tunnel near junction)) with (((bit program) near line\$1) (conduct\$3 near (layer\$1 film\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 17:36

L10	0	(black near diamond) with (between interpos\$3) with (MTJ (magnetic near tunnel near junction))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 17:37
L11	0	(black near diamond) and (between interpos\$3) and (MTJ (magnetic near tunnel near junction))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 17:39
L12	0	(black near diamond) with (MTJ (magnetic near tunnel near junction))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 17:37
L13	0	(black near diamond) and (MTJ (magnetic near tunnel near junction))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 17:39
L14	1126	(black near diamond)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 17:38
L15	204	14 and (low near k near (insulat\$3 oxide dielectric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 17:38
L16	0	15 and (MTJ (magnetic near tunnel near junction))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 17:54
L17	278480	15 and ((bit program) near line\$1) (conduct\$3 near (layer\$1 film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 17:40
L18	116	15 and (((bit program) near line\$1) (conduct\$3 near (layer\$1 film\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 17:41

L19	2	15 and MRAM	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 17:59
L20	6089	MRAM (magnetic adj random adj access adj memory)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 18:00
L21	38	20 and ((low near k near (insulat\$3 oxide dielectric)) (black near diamond))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 18:03
S1	50	("20020105827" "20030048676" "2003008 6313" "5956267" "6005800" "6114719" "6 335890" "6368878" "6417561" "6430084" " 6475812" "6490217" "6509624" "6515897 " "6522579" "6525957" "6555858" "65672 99" "6590803" "6594191" "6621731" "666 1689" "6667899" "6693822" "6693826"). PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 12:06
S2	19	S1 and (MTJ (magnetic adj tunnel adj junction))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 12:32
S3	1	S2 and (low near k near dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 12:16
S4	12072	257/68,71,295-314,324-326,659.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 12:15
S5	2341	438/3,240.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 12:16

S6	13938	S4 or S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 12:16
S7	230	S6 and (MTJ (magnetic adj tunnel adj junction))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 12:22
S8	5	S7 and (low near k near dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 12:22
S9	0	S6 and ((MTJ (magnetic adj tunnel adj junction)) with (low near k near dielectric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 12:30
S10	446027	"257"/\$.ccls. "438"/\$.ccls. "365"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 12:21
S11	0	S10 and ((MTJ (magnetic adj tunnel adj junction)) with (low near k near dielectric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 12:22
S12	1222	S10 and (MTJ (magnetic adj tunnel adj junction))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 12:22
S13	19	S12 and (low near k near dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 12:33
S14	0	((MTJ (magnetic adj tunnel adj junction)) with (low near k near dielectric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 12:30

S15	2	((MTJ (magnetic adj tunnel adj junction)) same (low near k near dielectric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 12:40
S16	2320	(MTJ (magnetic adj tunnel adj junction))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 12:42
S17	19	S16 and (low near k near dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 12:33
S18	2	((MTJ (magnetic adj tunnel adj junction)) same (low near k near (insulat\$3 oxide dielectric)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 12:43
S19	154	(MTJ (magnetic near tunnel near junction)) near stack\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 12:42
S20	172	(MTJ (magnetic near tunnel near junction)) near stack\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 16:18
S21	10	S20 and (low near k near (insulat\$3 oxide dielectric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/11 16:20